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# United States Patent [19] Kito

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[54] **METHOD FOR WIRING OF A SEMICONDUCTOR DEVICE**

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## Related U.S. Application Data

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[58] Field of Search ..... 438/584, 586, 438/597, 598, 599, 618, 621

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## [57] ABSTRACT

A perimeter gate wiring **52** comprises a contact portion **54** and an interconnecting portion **56** having narrower width than the contact portion **54** which connects the contact portion **54** mutually. And the perimeter gate wiring **52** is connected electrically with the gate perimeter portion **66** at the contact portion **54**. A source wiring perimeter portion **58** comprises a contact portion **60** and an interconnecting portion **62** having narrower width than the contact portion **60** which connects the contact portion **60** mutually. And the source wiring perimeter portion **58** is connected electrically with a perimeter diffusion layer **74** in the contact portion **60**. The contact portion **54** of the perimeter gate wiring **52** and the interconnecting portion **62** of the source wiring perimeter portion **58** are provided adjacently. Also, the interconnecting portion **56** of the perimeter gate wiring **52** and the contact portion **60** of the source wiring perimeter portion **58** are provided with one another adjacently. So that, it is possible to narrow a width of both the perimeter gate wiring **52** and the source wiring perimeter portion **58** with maintaining contact between the gate perimeter portion **66** and the like.

**4 Claims, 14 Drawing Sheets**

